

Peter Zaumseil

List of Publications by Year in descending order

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18
papers

269
citations

933447

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940533

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docs citations

18
times ranked

391
citing authors

#	ARTICLE	IF	CITATIONS
1	Fully coherent growth of Ge on free-standing Si(001) nanomesas. Physical Review B, 2014, 89, .	3.2	32
2	Photodetection in Hybrid Single-Layer Graphene/Fully Coherent Germanium Island Nanostructures Selectively Grown on Silicon Nanotip Patterns. ACS Applied Materials & Interfaces, 2016, 8, 2017-2026.	8.0	32
3	Ternary and quaternary Ni(Si)Ge(Sn) contact formation for highly strained Ge p- and n-MOSFETs. Semiconductor Science and Technology, 2015, 30, 055003.	2.0	28
4	Dislocation-free Ge Nano-crystals via Pattern Independent Selective Ge Heteroepitaxy on Si Nano-Tip Wafers. Scientific Reports, 2016, 6, 22709.	3.3	25
5	Temperature dependence of strain-phonon coefficient in epitaxial Ge/Si(001): A comprehensive analysis. Journal of Raman Spectroscopy, 2020, 51, 989-996.	2.5	20
6	Schottky barrier tuning via dopant segregation in NiGeSn-GeSn contacts. Journal of Applied Physics, 2017, 121, .	2.5	20
7	A complex x-ray characterization of heteroepitaxial silicon/insulator/silicon(111) structures. Journal of Applied Physics, 2008, 104, .	2.5	16
8	Compliant Si nanostructures on SOI for Ge nanoheteroepitaxy—A case study for lattice mismatched semiconductor integration on Si(001). Journal of Applied Physics, 2012, 112, 043506.	2.5	13
9	About the strain state of different metal oxide layers epitaxially grown on Si(100). Journal Physics D: Applied Physics, 2011, 44, 055403.	2.8	12
10	Fabrication of GeSn-multiple quantum wells by overgrowth of Sn on Ge by using molecular beam epitaxy. Applied Physics Letters, 2015, 107, .	3.3	12
11	Sn migration control at high temperature due to high deposition speed for forming high-quality GeSn layer. Applied Physics Express, 2016, 9, 031201.	2.4	11
12	Selective growth of fully relaxed GeSn nano-islands by nanoheteroepitaxy on patterned Si(001). Applied Physics Letters, 2016, 109, .	3.3	10
13	Morphological evolution of Ge/Si nano-strips driven by Rayleigh-like instability. Applied Physics Letters, 2018, 112, 022101.	3.3	10
14	Composition analysis and transition energies of ultrathin Sn-rich GeSn quantum wells. Physical Review Materials, 2020, 4, .	2.4	10
15	Photoluminescence from GeSn nano-heterostructures. Nanotechnology, 2018, 29, 415702.	2.6	9
16	Characterization of reclaimed GaAs substrates and investigation of reuse for thin film InGaAlP LED epitaxial growth. Journal of Applied Physics, 2016, 120, 045301.	2.5	7
17	Gate stack and Ni(SiGeSn) metal contacts formation on low bandgap strained (Si)Ge(Sn) semiconductors. , 2018, , .		2
18	Structural analysis of a phosphide-based epitaxial structure with a buried oxidized AlAs sacrificial layer. Journal of Applied Physics, 2017, 121, 215303.	2.5	0